

P-channel TrenchMOS extremely low level FET Rev. 04 — 25 October 2010 P

Product data sheet

Product profile 1.

1.1 General description

Extremely low level P-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

Load switching

1.2 Features and benefits

Low conduction losses due to low on-state resistance

1.3 Applications

Battery management

1.4 Quick reference data

| Table 1. | Quick reference data | | | | | |
|-------------------|----------------------------------|--|-----|-----|-----------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 150 °C | - | - | -30 | V |
| I _D | drain current | $T_{sp} = 25 \text{ °C}; V_{GS} = -10 \text{ V};$ see <u>Figure 1</u> ; see <u>Figure 3</u> | - | - | -14. 9 | А |
| P _{tot} | total power dissipation | T _{sp} = 25 °C; see <u>Figure 2</u> | - | - | 6.9 | W |
| Static cha | aracteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = -10 V; I _D = -9.2 A; T _j = 25 °C; see <u>Figure 9</u> | - | 16 | 19 | mΩ |
| Dynamic | characteristics | | | | | |
| Q _{GD} | gate-drain charge | $V_{GS} = -10 \text{ V}; I_D = -9.2 \text{ A};$ $V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u> | - | 7 | - | nC |

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Pinning information 2.

| Table 2. | Pinning | information | | |
|----------|---------|-------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | S | source | | _ |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | G↓ŢŢ |
| 5 | D | drain | | |
| 6 | D | drain | SOT96-1 (SO8) | S 001aaa025 |
| 7 | D | drain | | |
| 8 | D | drain | | |

Ordering information 3.

| Table 3. Ordering in | nformation | | |
|----------------------|------------|---|---------|
| Type number | Package | | |
| | Name | Description | Version |
| PMK30EP | SO8 | plastic small outline package; 8 leads; body width 3.9 mm | SOT96-1 |

Limiting values 4.

Table 4. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|--|-----|-------|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 150 °C | - | -30 | V |
| V _{DGR} | drain-gate voltage | 25 °C \leq T _j \leq 150 °C; R _{GS} = 20 k Ω | - | -30 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| I _D | drain current | $T_{sp} = 25 \text{ °C}; V_{GS} = -10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$ | - | -14.9 | А |
| | | T_{sp} = 100 °C; V_{GS} = -10 V; see <u>Figure 1</u> | - | -7.5 | А |
| I _{DM} | peak drain current | $T_{sp} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s}; \text{ see } \frac{\text{Figure } 3}{10 \mu\text{s}}$ | - | -28.8 | А |
| P _{tot} | total power dissipation | T _{sp} = 25 °C; see <u>Figure 2</u> | - | 6.9 | W |
| T _{stg} | storage temperature | | -55 | 150 | °C |
| Tj | junction temperature | | -55 | 150 | °C |
| Source-dra | in diode | | | | |
| I _S | source current | T _{sp} = 25 °C | - | -5.8 | А |
| I _{SM} | peak source current | $T_{sp} = 25 \text{ °C}$; pulsed; $t_p \le 10 \mu\text{s}$ | - | -23 | А |

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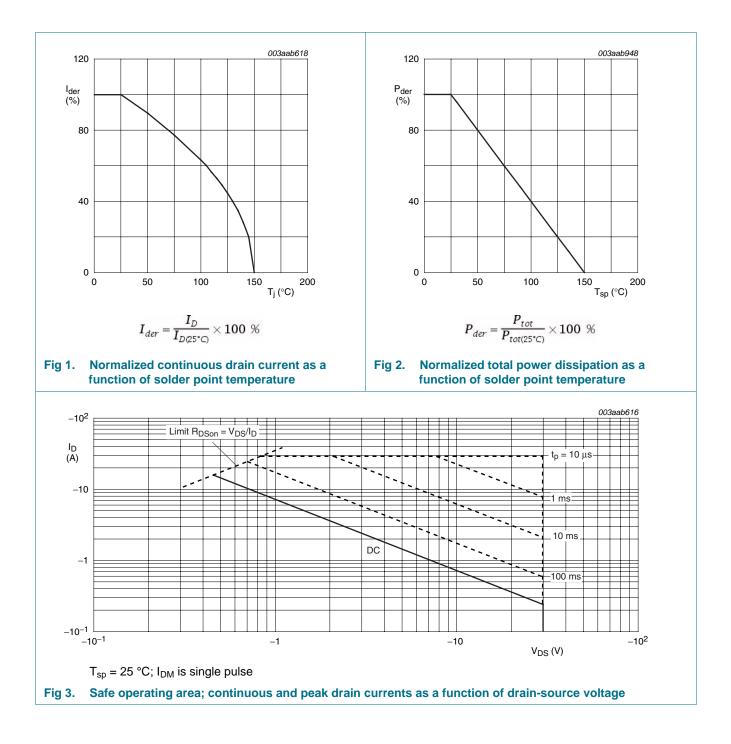
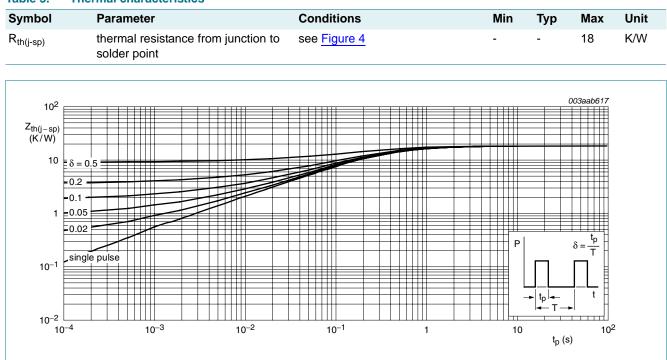


Fig 4.

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5. Thermal characteristics



Transient thermal impedance from junction to solder point as a function of pulse duration

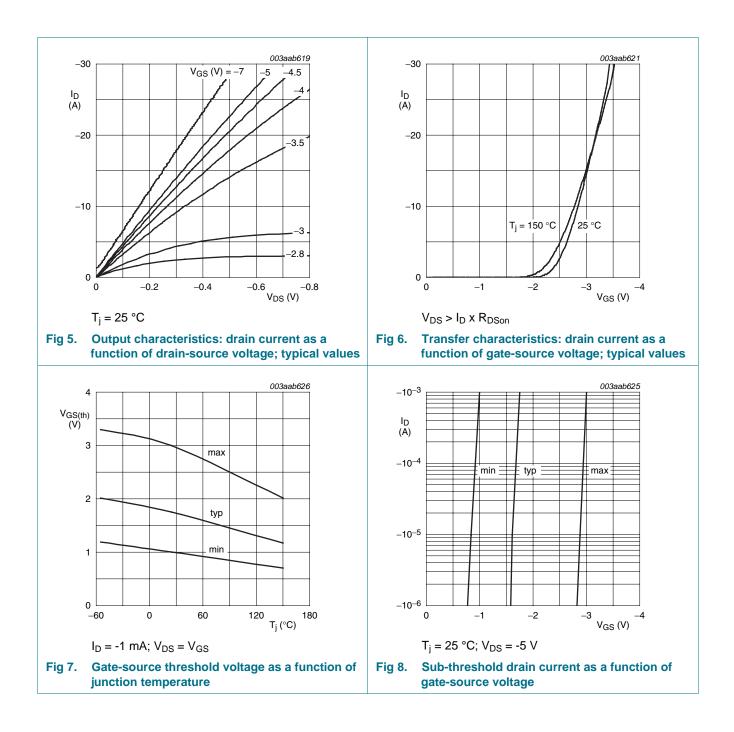
Table 5. Thermal characteristics

6. Characteristics

| Table 6. | Characteristics | | | | | |
|---|---|---|------|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _{(BR)DSS} drain-source breakdown | $I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$ | -30 | - | - | V | |
| | voltage | $I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^{\circ}C$ | -27 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | $I_D = -250 \ \mu A; V_{DS} = V_{GS}; T_j = 25 \ ^{\circ}C;$ see <u>Figure 7</u> ; see <u>Figure 8</u> | -1 | - | -3 | V |
| | | $I_D = -250 \ \mu A; V_{DS} = V_{GS}; T_j = 150 \ ^\circC;$ see Figure 7; see Figure 8 | -0.7 | - | - | V |
| | | $I_D = -250 \ \mu A; V_{DS} = V_{GS}; T_j = -55 \ ^{\circ}C;$ see <u>Figure 7</u> ; see <u>Figure 8</u> | - | - | -3.3 | V |
| I _{DSS} | drain leakage current | V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 °C | - | - | -1 | μA |
| | | V_{DS} = -30 V; V_{GS} = 0 V; T_j = 70 °C | - | - | -10 | μA |
| I _{GSS} | gate leakage current | $V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | - | -100 | nA |
| | | V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = -10 V; I _D = -9.2 A; T _j = 25 °C; see <u>Figure 9</u> | - | 16 | 19 | mΩ |
| | | V_{GS} = -10 V; I _D = -9.2 A; T _j = 150 °C; see <u>Figure 9</u> | - | 25 | 31 | mΩ |
| | $V_{GS} = -4.5 \text{ V}; I_D = -7.3 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 9</u> | - | 24 | 30 | mΩ | |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | I _D = -9.2 A; V _{DS} = -15 V; V _{GS} = -10 V; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | 50 | - | nC |
| Q_{GS} | gate-source charge | I _D = -9.2 A; V _{DS} = -15 V; V _{GS} = -10 V; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | 7 | - | nC |
| Q_{GD} | gate-drain charge | I _D = -9.2 A; V _{DS} = -15 V; V _{GS} = -10 V; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | 7 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | I _D = -9.2 A; V _{DS} = -15 V; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | - | -2.5 | - | V |
| C _{iss} | input capacitance | V_{DS} = -25 V; V_{GS} = 0 V; f = 1 MHz; | - | 2240 | - | pF |
| C _{oss} | output capacitance | $T_j = 25 \text{ °C}; \text{ see } Figure 13$ | - | 325 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 220 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -15 V; R_{L} = 6 Ω ; V_{GS} = -10 V; | - | 10 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 \ ^{\circ}C$ | - | 8 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 56 | - | ns |
| t _f | fall time | | - | 21 | - | ns |
| Source-d | rain diode | | | | | |
| V_{SD} | source-drain voltage | I _S = -3.45 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 14</u> | - | -0.8 | -1.2 | V |

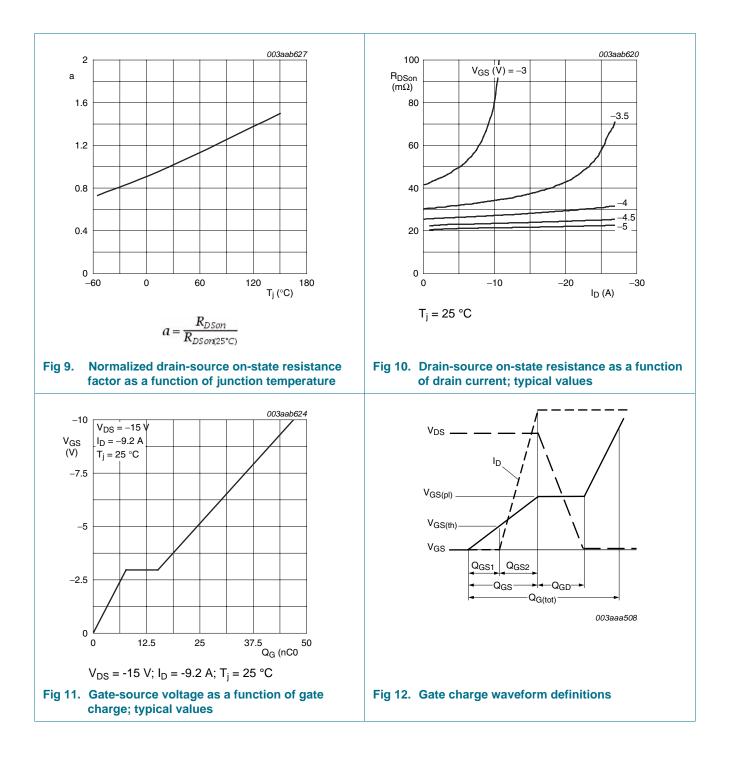
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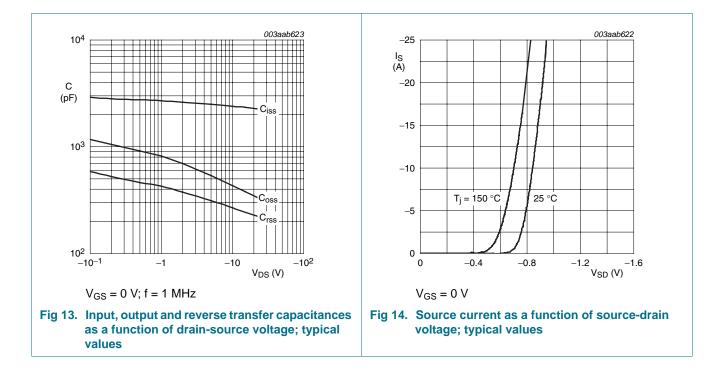
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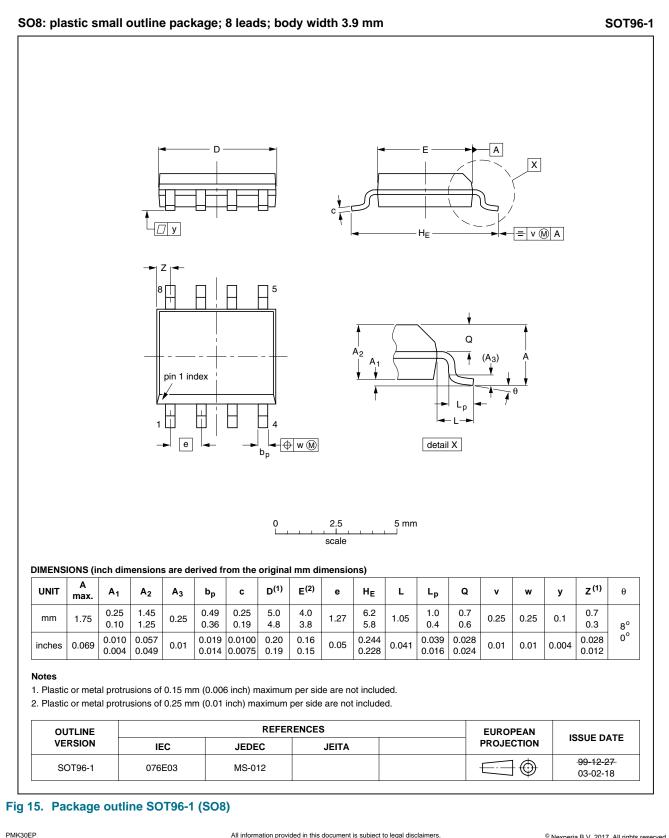


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Package outline 7.



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8. Revision history

| Table 7. | Revision history | |
|----------|-------------------------|--|
|----------|-------------------------|--|

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|-----------------------------------|--------------------|---------------|-------------|
| PMK30EP v.4 | 20101025 | Product data sheet | - | PMK30EP v.3 |
| Modifications: | Various chang | jes to content. | | |
| PMK30EP v.3 | 20100429 | Product data sheet | - | - |

9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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